

# EH2545TTS-57.000M TR [↗](#)



## ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD) 57.000MHz ±50ppm 0°C to +70°C

## ELECTRICAL SPECIFICATIONS

Nominal Frequency	57.000MHz
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	5.0Vdc ±10%
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ±5(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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## MECHANICAL DIMENSIONS (all dimensions in millimeters)



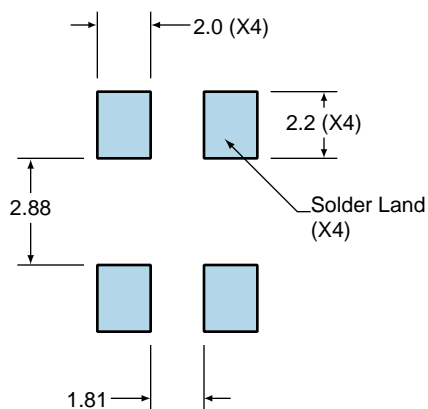
PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	57.000M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

## Suggested Solder Pad Layout

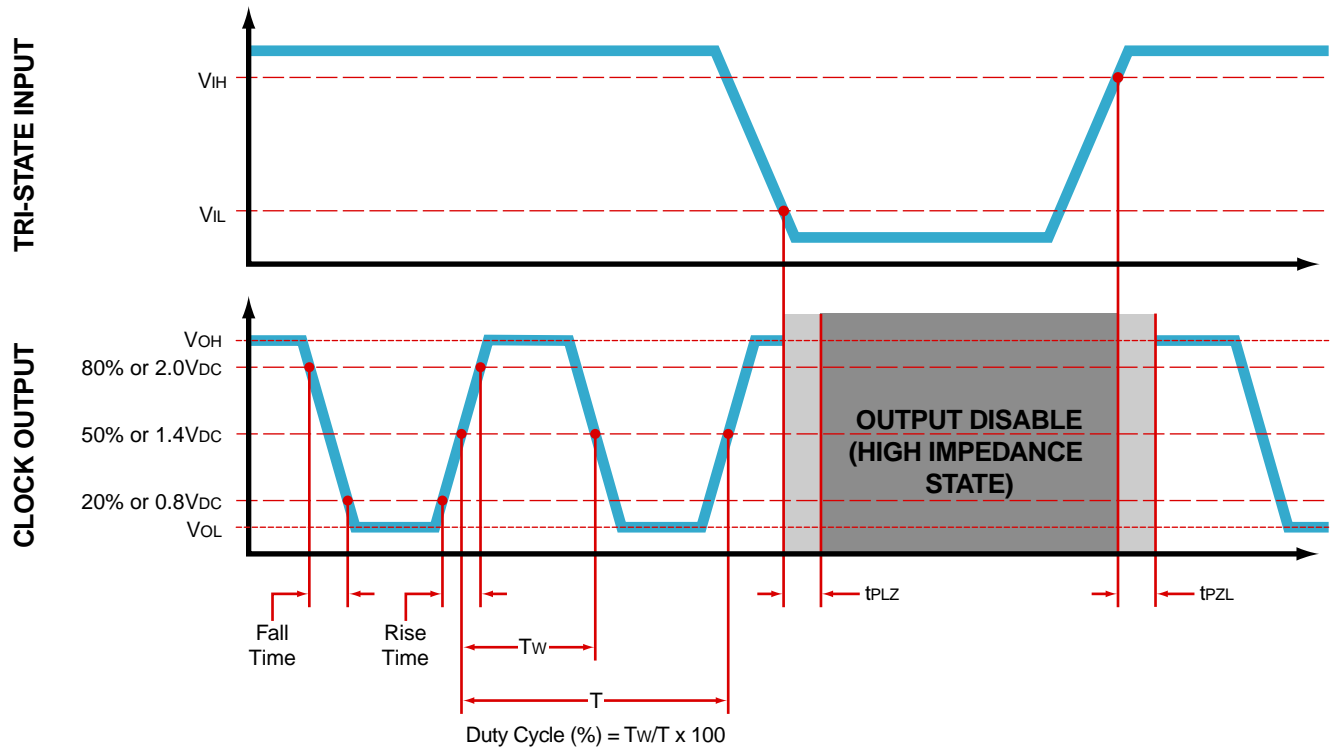
All Dimensions in Millimeters



All Tolerances are ±0.1

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## OUTPUT WAVEFORM & TIMING DIAGRAM

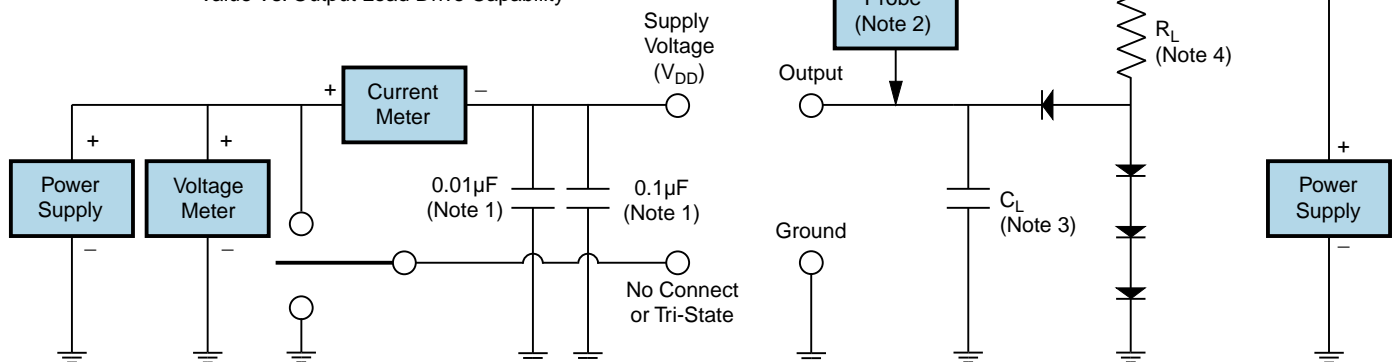


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## Test Circuit for TTL Output

Output Load Drive Capability	$R_L$ Value (Ohms)	$C_L$ Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

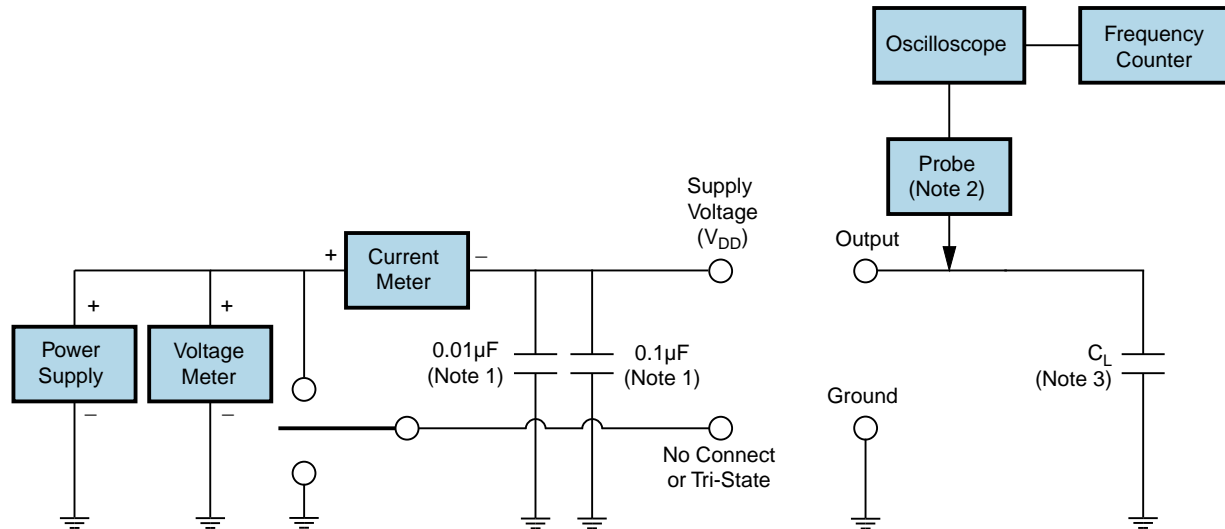
Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value  $R_L$  is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

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## Test Circuit for CMOS Output



Note 1: An external  $0.1\mu\text{F}$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu\text{F}$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

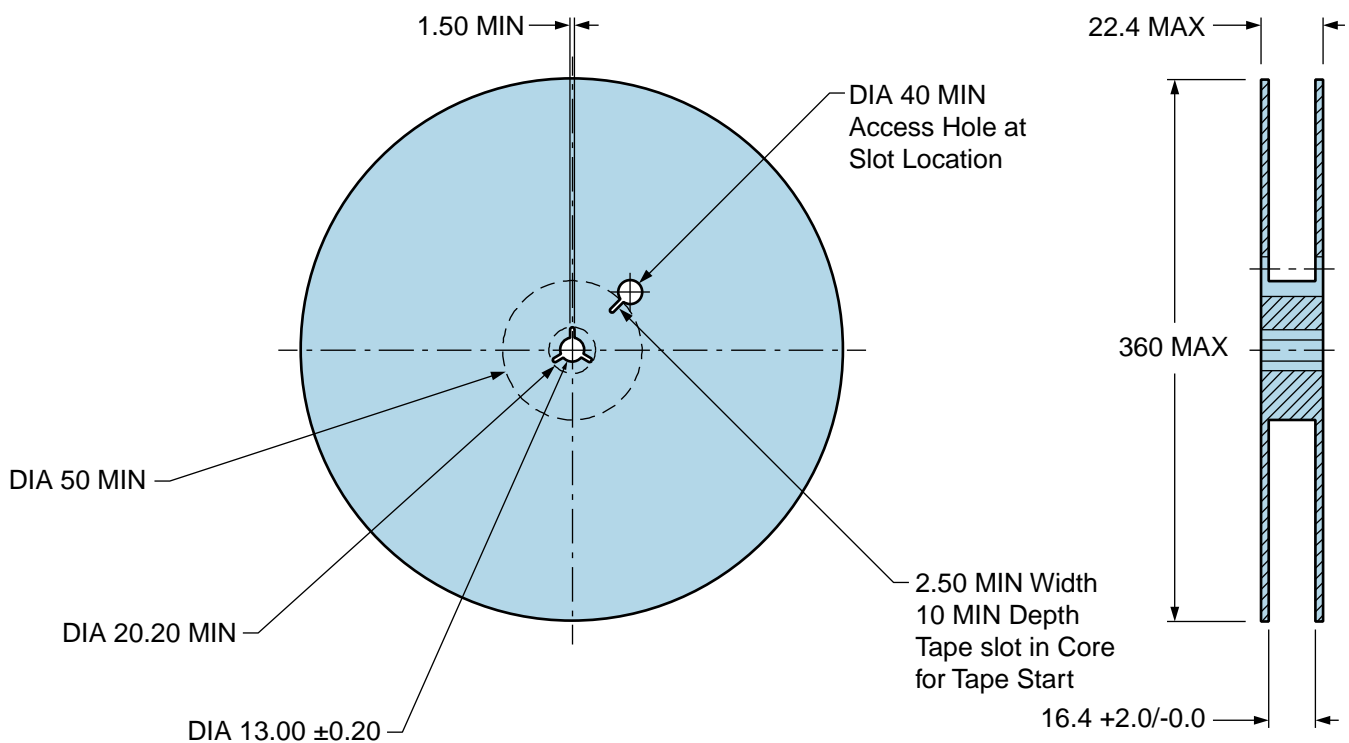
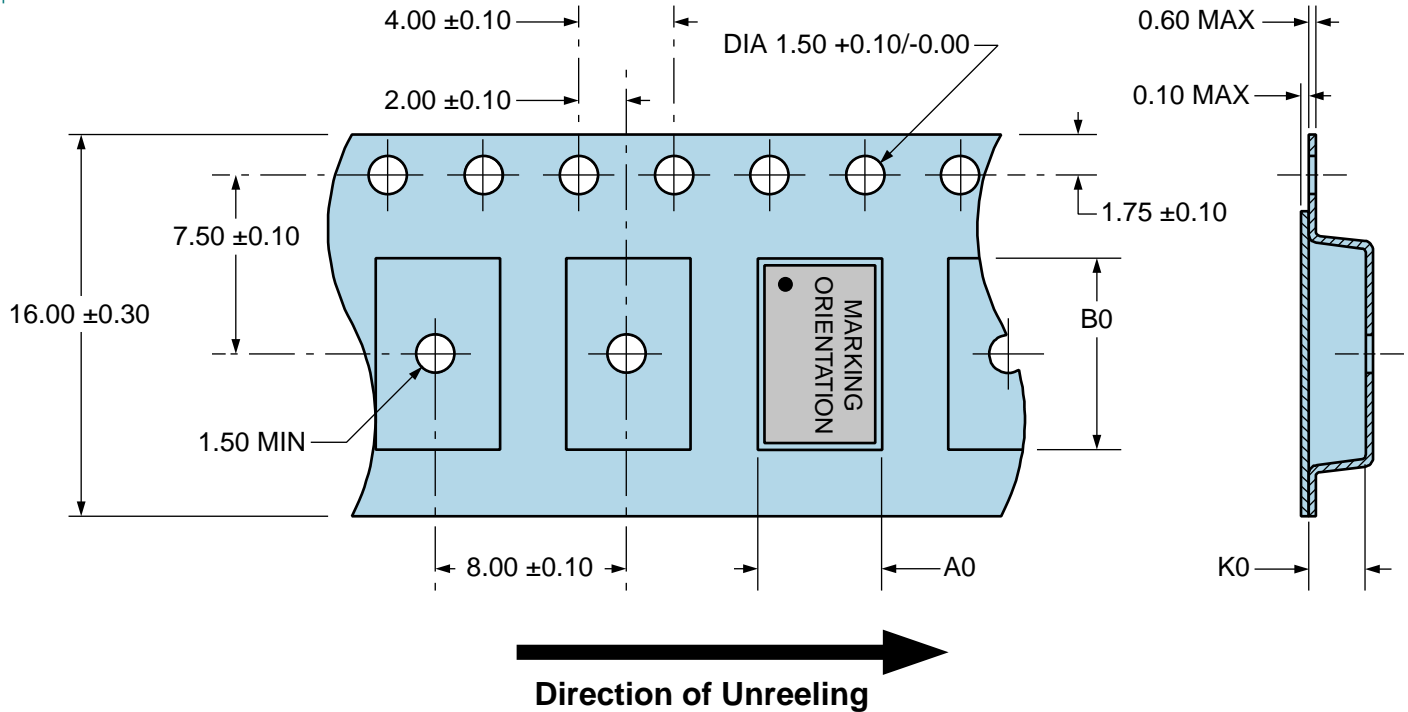
Note 2: A low capacitance ( $<12\text{pF}$ ), 10X attenuation factor, high impedance ( $>10\text{Mohms}$ ), and high bandwidth ( $>300\text{MHz}$ ) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

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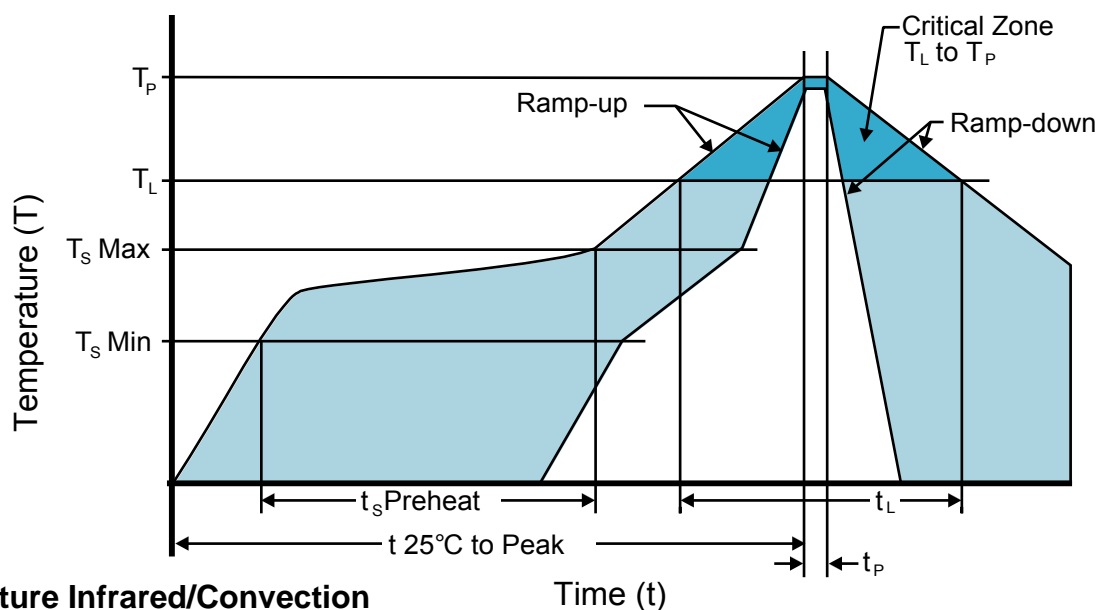
## Tape & Reel Dimensions

Quantity Per Reel: 1,000 units  
 All Dimensions in Millimeters  
 Compliant to EIA-481



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## Recommended Solder Reflow Methods

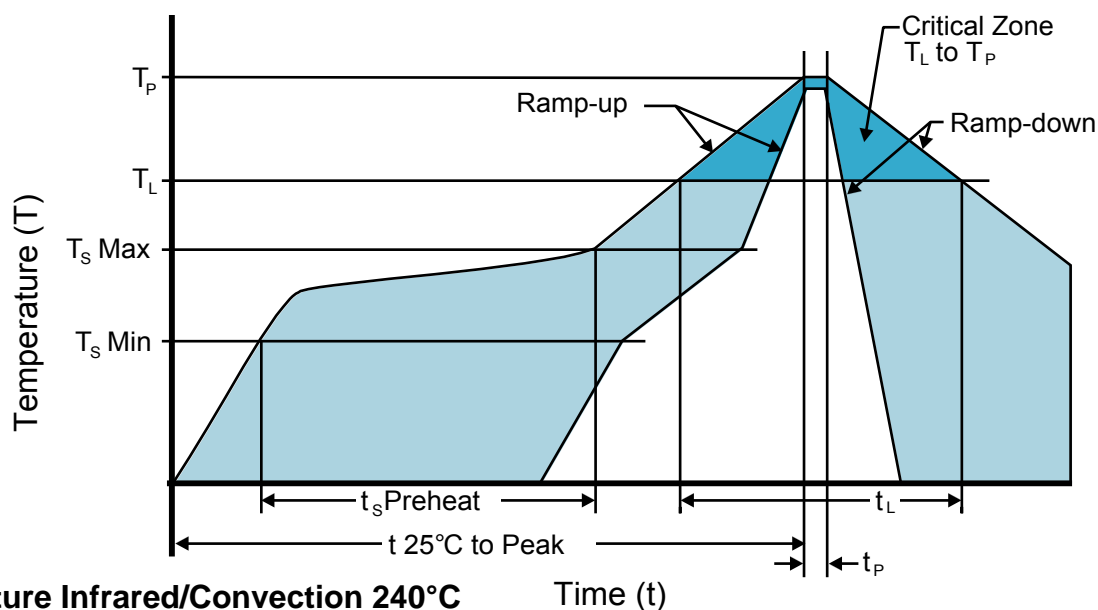


### High Temperature Infrared/Convection

<b>Ts MAX to TL (Ramp-up Rate)</b>	3°C/Second Maximum
<b>Preheat</b>	
- Temperature Minimum (Ts MIN)	150°C
- Temperature Typical (Ts TYP)	175°C
- Temperature Maximum (Ts MAX)	200°C
- Time (ts MIN)	60 - 180 Seconds
<b>Ramp-up Rate (TL to TP)</b>	3°C/Second Maximum
<b>Time Maintained Above:</b>	
- Temperature (TL)	217°C
- Time (tL)	60 - 150 Seconds
<b>Peak Temperature (TP)</b>	260°C Maximum for 10 Seconds Maximum
<b>Target Peak Temperature (TP Target)</b>	250°C +0/-5°C
<b>Time within 5°C of actual peak (tP)</b>	20 - 40 Seconds
<b>Ramp-down Rate</b>	6°C/Second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	8 Minutes Maximum
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

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## Recommended Solder Reflow Methods



### Low Temperature Infrared/Convection 240°C

$T_s$  MAX to  $T_L$  (Ramp-up Rate) 5°C/Second Maximum

#### Preheat

- Temperature Minimum ( $T_s$  MIN) N/A  
 - Temperature Typical ( $T_s$  TYP) 150°C  
 - Temperature Maximum ( $T_s$  MAX) N/A  
 - Time ( $t_s$  MIN) 60 - 120 Seconds

Ramp-up Rate ( $T_L$  to  $T_P$ ) 5°C/Second Maximum

#### Time Maintained Above:

- Temperature ( $T_L$ ) 150°C  
 - Time ( $t_L$ ) 200 Seconds Maximum

Peak Temperature ( $T_P$ ) 240°C Maximum

Target Peak Temperature ( $T_P$  Target) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak ( $t_p$ ) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Additional Notes Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)